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APPLICATION NO. **NEW**

FILING DATE
January 25, 2002

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10/054823 U.S. PAT.

[illegible][illegible]

OTHER DOCUMENTS (Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.)

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 JUL 02 2002
 PATENT OFFICE
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 APPLICATION NO.
 10/054,823

 APPLICANT
 Hironori MATSUMOTO, et al.

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 January 25, 2002

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 2811

U.S. PATENT DOCUMENTS

EXAMINER	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	5,323,053	1994-06-21	Luryi, et al.			
	3,964,084	1976-06-15	Andrews, Jr., et al			
	4,662,058	1987-05-05	Cirillo, Jr. et al			
	5,956,137	1999-09-21	Lim, et al.			
	6,122,494	2000-09-19	Tuttle			
	5,731,691	1998-03-24	Noto			
	5,225,359	1993-07-06	DeLong			

FOREIGN PATENT DOCUMENTS

EXAMINER	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						YES	NO
	WO 00/74126 A1	2000-12-07	PCT				
	EP 0 702 316 A1	1996-03-20	EUROPE				
	EP 0 831 415 A2	1998-03-25	EUROPE				
	EP 0 902 476 A1	1999-03-17	EUROPE				
	EP 0 580 242 A1	1994-01-26	EUROPE				

OTHER DOCUMENTS (Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issues number(s), publisher, city and/or country where published.)

"A New BiCMOS Gate Array Cell with Diode Connected Bipolar Driver" T. HORIUCHI, et al., IEEE 1990 Bipolar Circuits and Technology Mtg. pp. 124-127

"Metal Silicide Schottky Barrier Diodes", C. M. HSIEH IBM Technical Disclosure Bulletin Vol. 21. No. 3 August 1978, pg. 1026

"A 0.4-Micron Fully Complementary BiCMOS Technology for Advanced Logic and Microprocessor Applications" Shih Wei Sun, et al., IEDM Dec. 8-11, 1991, pp. 91-85-88

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Paula D. Laine 10/30/02

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